

**AMENDMENTS TO THE SPECIFICATION:**

Please replace paragraph [0061] with the following amended paragraph:

Fig. 13 is a characteristic diagram showing a relationship between  
*B*  $(C_{MIN}+C_{MIS})/C_{MIS}$  of the semiconductor involatile nonvolatile storage element  
according to the first embodiment of the invention shown in Fig. 2I and a distance  
114(h) between a bottom face of a first conductor layer and upper faces of a third and  
a fourth conductor;